

Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

■ Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

■ Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

■ Maximum ratings and characteristic Absolute maximum ratings

● (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V _{DS}	500	V
Continuous drain current	I _D	±6	A
Pulsed drain current	I _{D(puls)}	±24	A
Gate-source voltage	V _{GS}	±30	V
Repetitive or non-repetitive	I _{AR} *2	6	A
Maximum Avalanche Energy	E _{AS} *1	115	mJ
Maximum Drain-Source dV/dt	dV _{DS} /dt *4	20	kV/μs
Peak Diode Recovery dV/dt	dV/dt *3	5	kV/μs
Max. power dissipation	P _D	T _a =25°C	2.02
		T _c =25°C	90
Operating and storage temperature range	T _{ch}	+150	°C
	T _{stg}	-55 to +150	°C

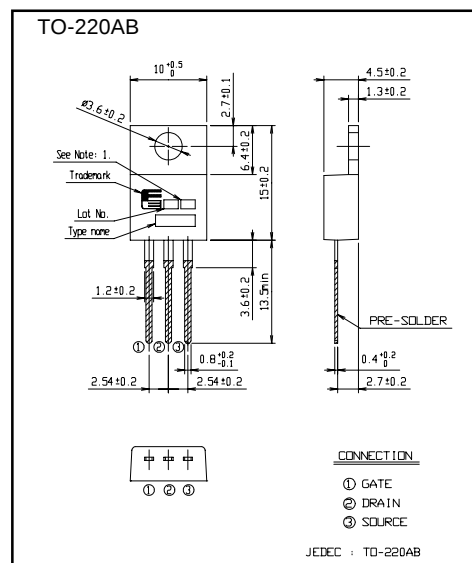
*1 L=5.90mH, V_{CC}=50V, See to Avalanche Energy Graph *2 T_{ch}≤150°C*3 I_F≤-I_D, -di/dt=50A/μs, V_{CC}≤BV_{DSS}, T_{ch}≤150°C *4 V_{DS}≤500V● Electrical characteristics (T_c =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V(BR) _{DSS}	I _D =250μA V _{GS} =0V	500			V
Gate threshold voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =500V V _{GS} =0V T _{ch} =25°C			25	μA
		V _{DS} =400V V _{GS} =0V T _{ch} =125°C			250	
Gate-source leakage current	I _{GSS}	V _{GS} =±30V V _{DS} =0V		10	100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =3A V _{GS} =10V		1.15	1.50	Ω
Forward transconductance	g _{fs}	I _D =3A V _{DS} =25V	2.5	5		S
Input capacitance	C _{iss}	V _{DS} =25V		430	675	pF
Output capacitance	C _{oss}	V _{GS} =0V		60	90	
Reverse transfer capacitance	C _{rss}	f=1MHz		2.5	4.5	
Turn-on time t _{on}	td(on)	V _{CC} =300V I _D =3A		10	15	ns
	t _r	V _{GS} =10V		5	7.5	
Turn-off time t _{off}	td(off)	R _{GS} =10Ω		20	30	
	t _r			5	7.5	
Total Gate Charge	Q _G	V _{CC} =250V		15	22.5	nC
Gate-Source Charge	Q _{GS}	I _D =6A		6.5	10.5	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		2.5	4.5	
Avalanche capability	I _{AV}	L=5.9mH T _{ch} =25°C	6			A
Diode forward on-voltage	V _{SD}	I _F =6A V _{GS} =0V T _{ch} =25°C		1.00	1.50	V
Reverse recovery time	t _{rr}	I _F =6A V _{GS} =0V		0.5		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		1.7		μC

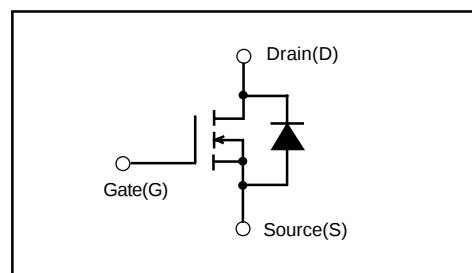
● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			1.39	°C/W
	R _{th(ch-a)}	channel to ambient			62.0	°C/W

■ Outline Drawings [mm]



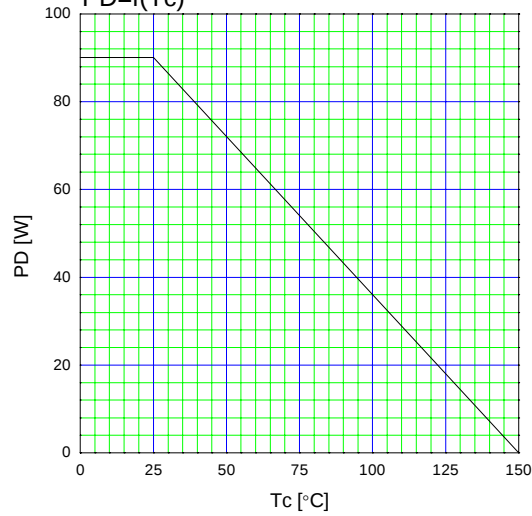
■ Equivalent circuit schematic



Characteristics

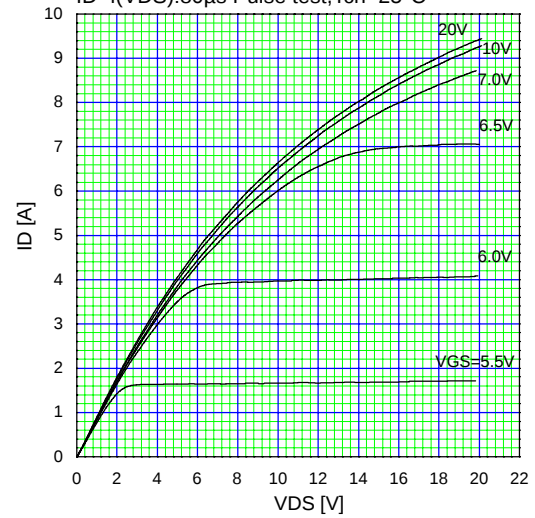
Allowable Power Dissipation

$$PD=f(T_c)$$



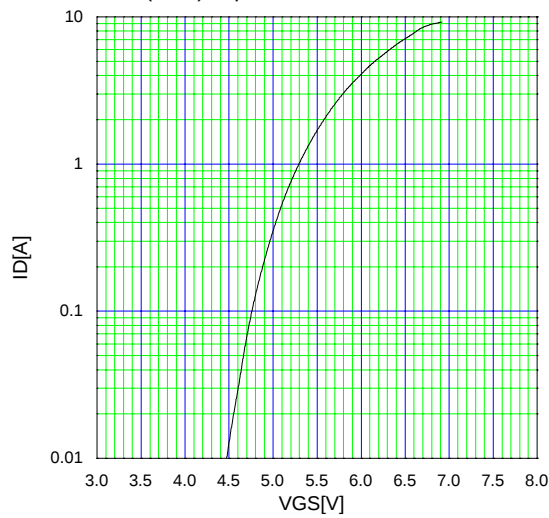
Typical Output Characteristics

$$ID=f(V_{DS}):80\mu\text{s Pulse test, } T_{ch}=25^{\circ}\text{C}$$



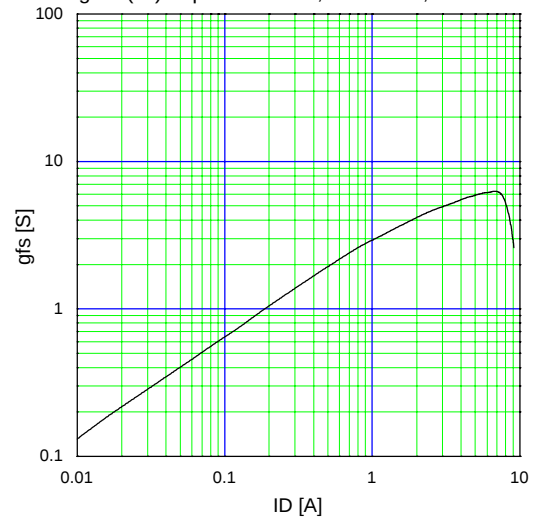
Typical Transfer Characteristic

$$ID=f(V_{GS}):80\mu\text{s Pulse test, } V_{DS}=25\text{V, } T_{ch}=25^{\circ}\text{C}$$



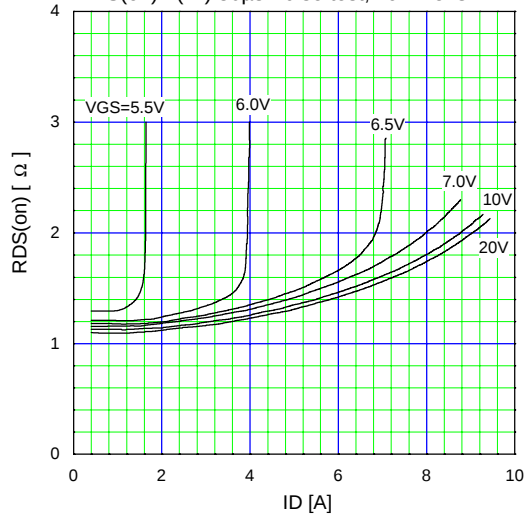
Typical Transconductance

$$g_{fs}=f(ID):80\mu\text{s Pulse test, } V_{DS}=25\text{V, } T_{ch}=25^{\circ}\text{C}$$



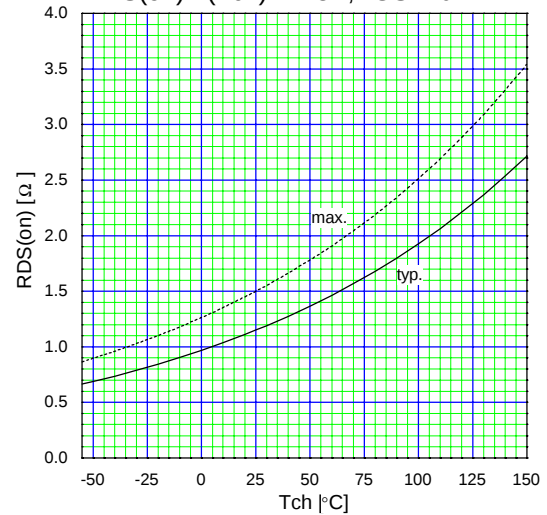
Typical Drain-Source on-state Resistance

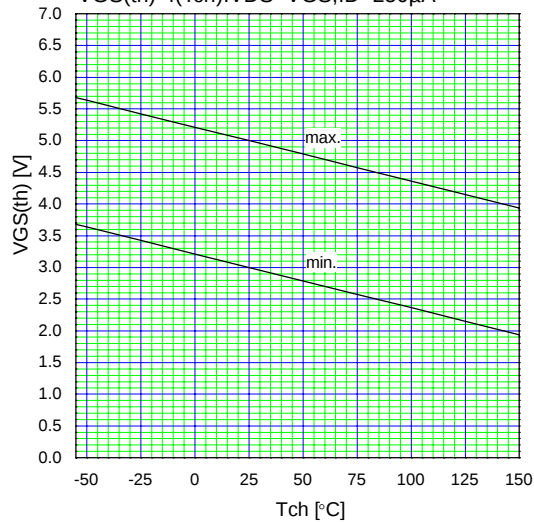
$$R_{DS(on)}=f(ID):80\mu\text{s Pulse test, } T_{ch}=25^{\circ}\text{C}$$



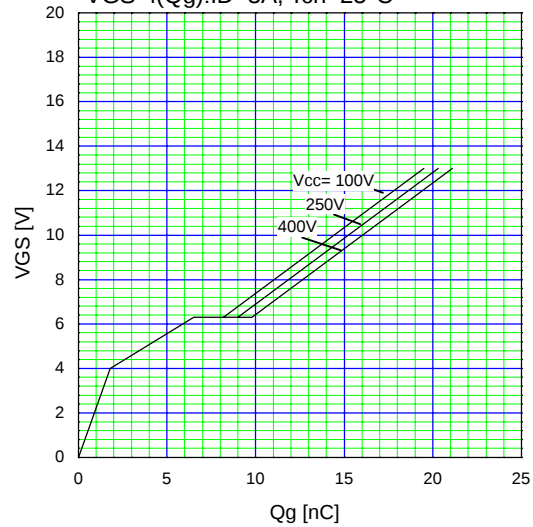
Drain-Source On-state Resistance

$$R_{DS(on)}=f(T_{ch}):ID=3\text{A, } V_{GS}=10\text{V}$$

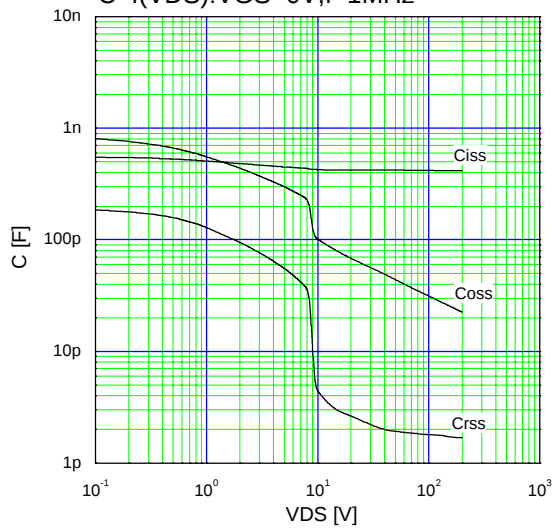


Gate Threshold Voltage vs. T_{ch}V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS},I_D=250μA

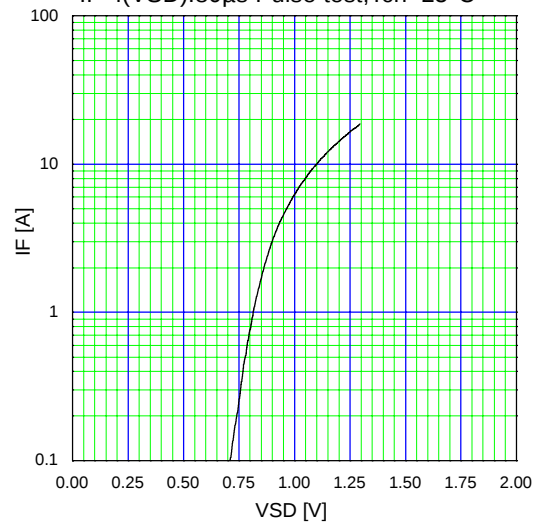
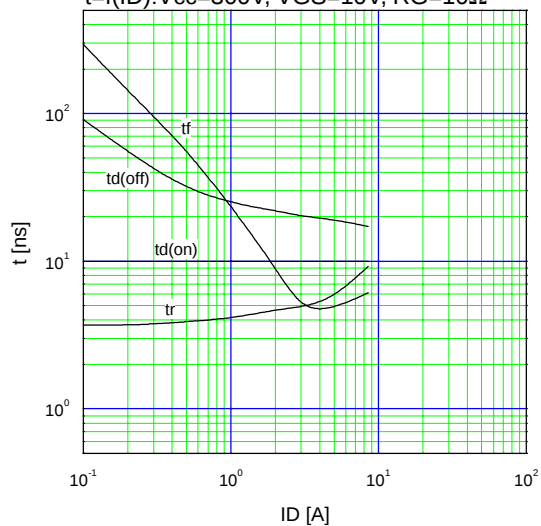
Typical Gate Charge Characteristics

V_{GS}=f(Q_g):I_D=3A, T_{ch}=25°C

Typical Capacitance

C=f(V_{DS}):V_{GS}=0V,f=1MHz

Typical Forward Characteristics of Reverse Diode

I_F=f(V_{SD}):80μs Pulse test,T_{ch}=25°CTypical Switching Characteristics vs. I_Dt=f(I_D):V_{CC}=300V, V_{GS}=10V, R_G=10ΩMaximum Avalanche Energy vs. starting T_{ch}E_{AS}=f(starting T_{ch}):V_{CC}=50V